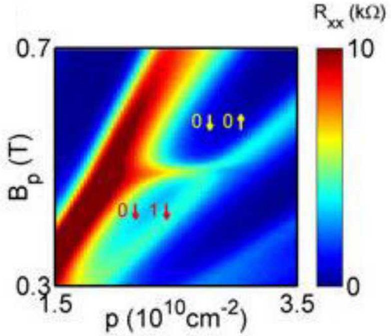
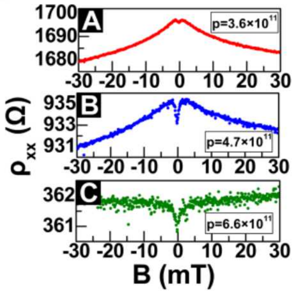
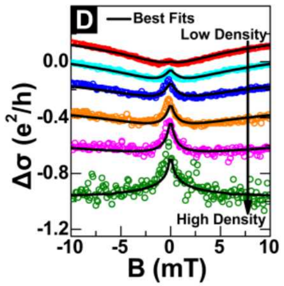
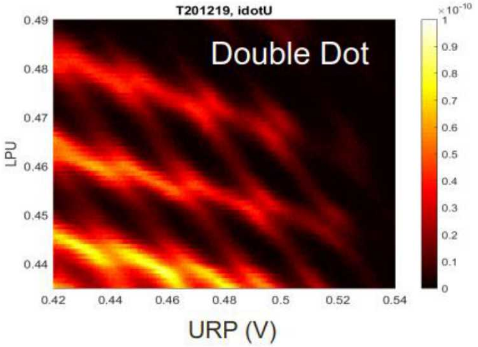
SAND2018-10043C

Ge/SiGe quantum electronic devices









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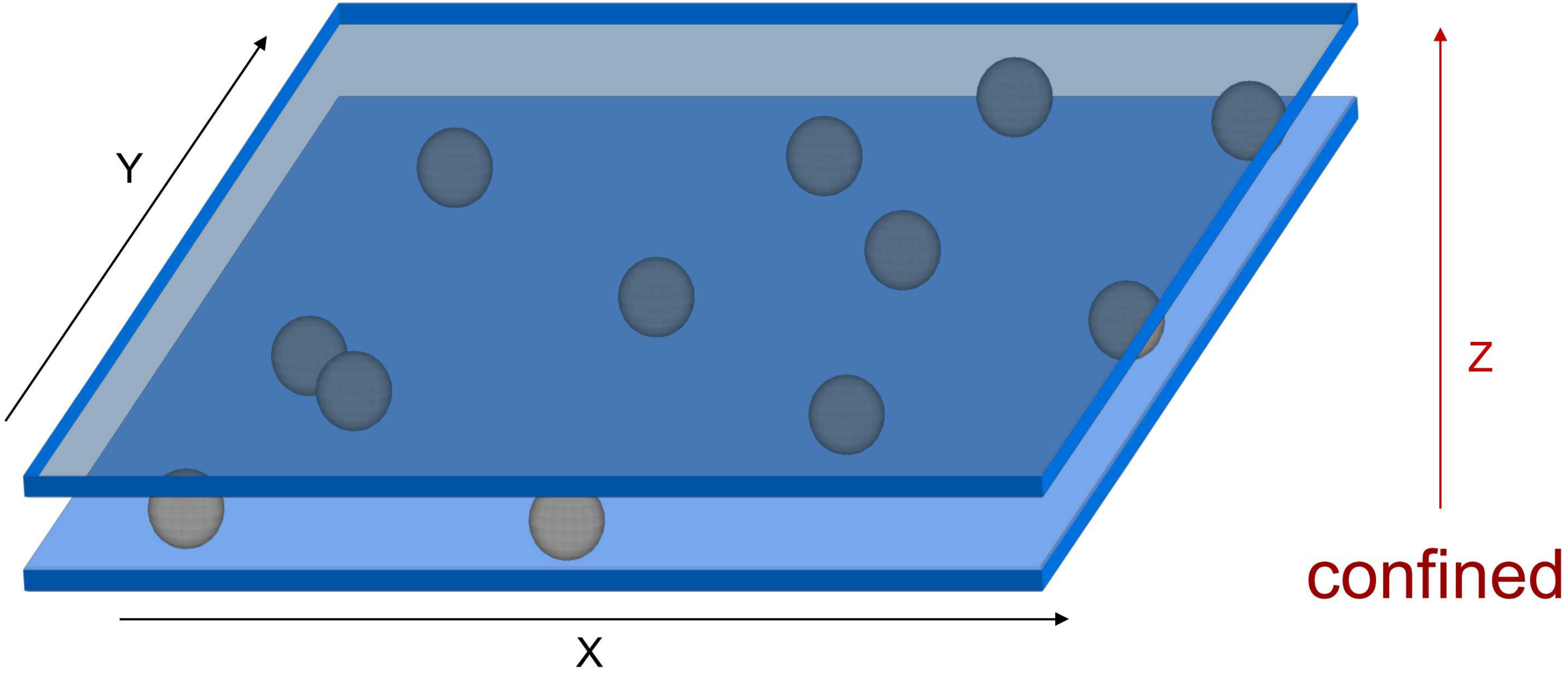
Outline

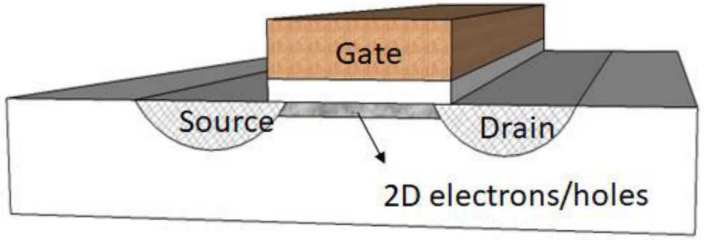
- Ge/SiGe heterostructures
- Device operation
- Properties of 2D holes in Ge/SiGe
- Quantum Hall ferromagnetic transition
- Spin qubits in Ge/SiGe
- Summary

2D electrons/holes

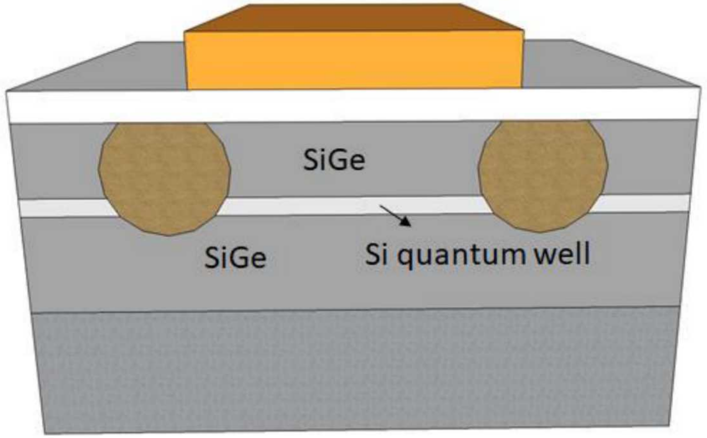


2D electrons in Si

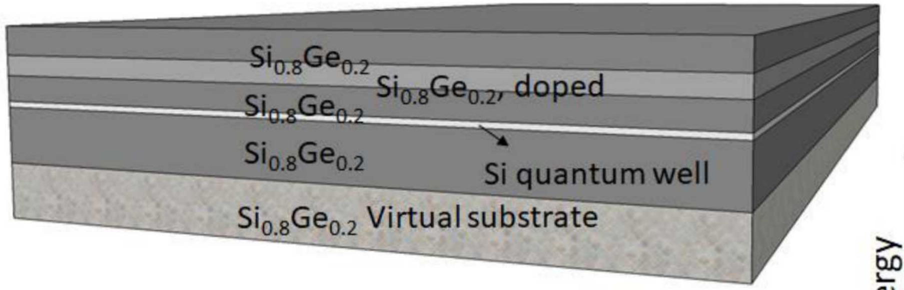
Si MOSFET

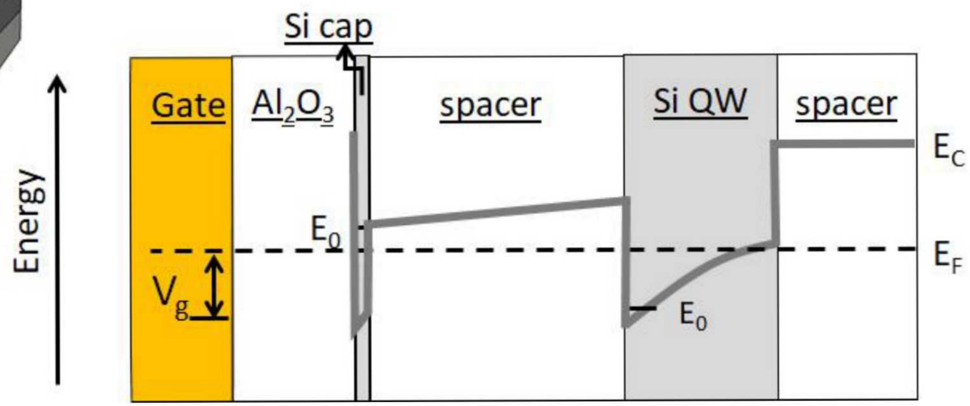


Undoped Si/SiGe HFET

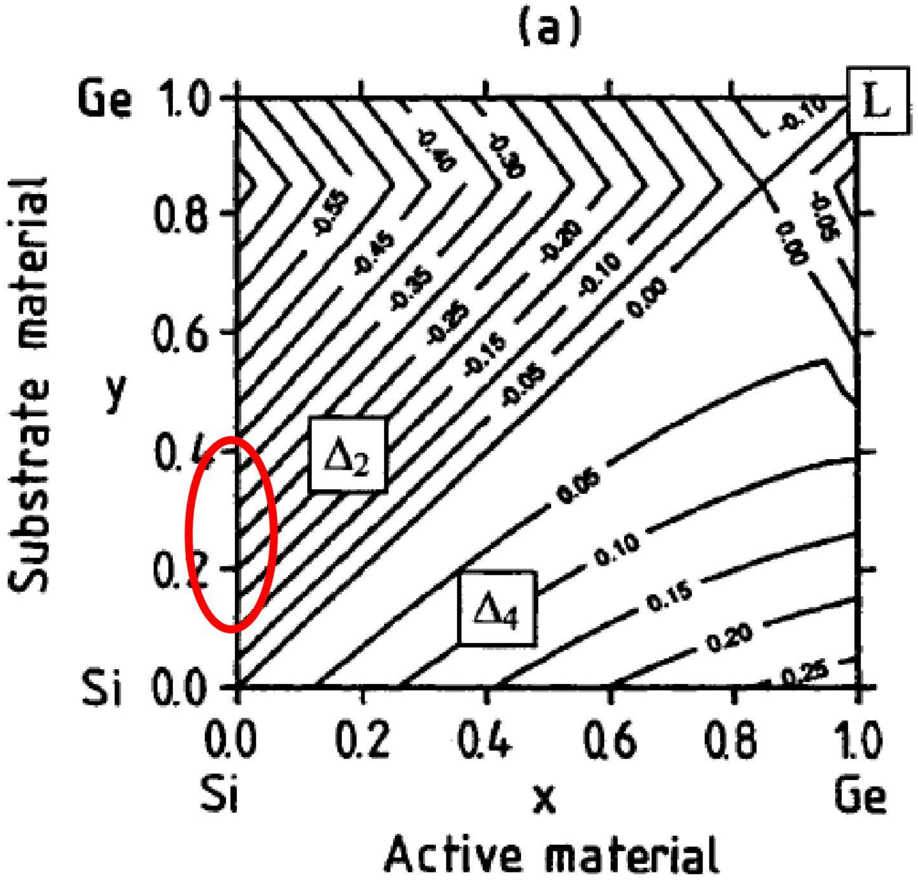


Modulation doped Si/SiGe

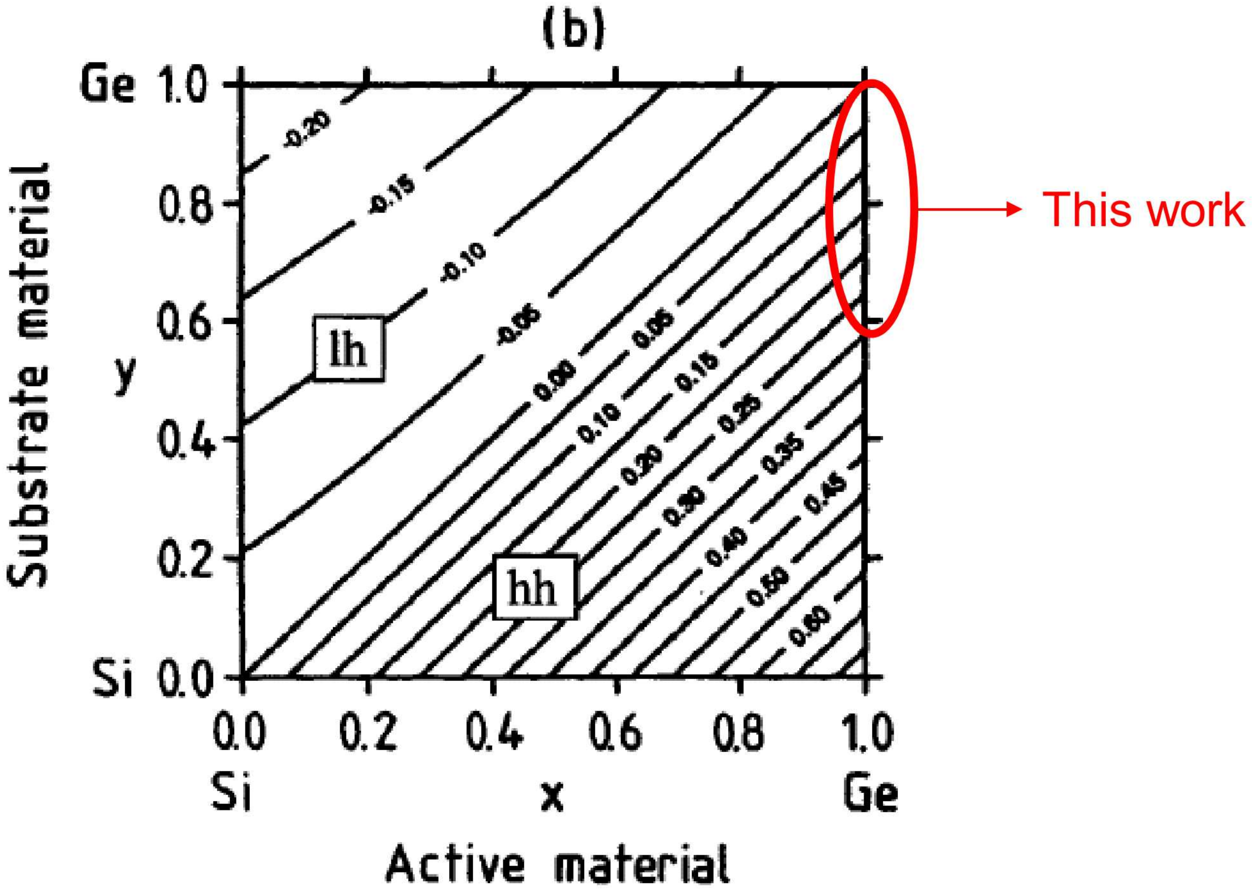




Band alignment of SiGe heterostructures



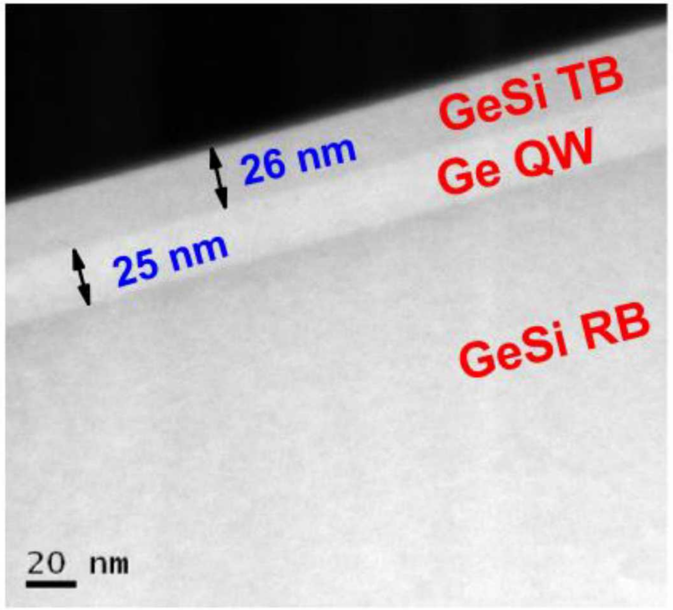
Conduction band
2D electrons in Si quantum wells

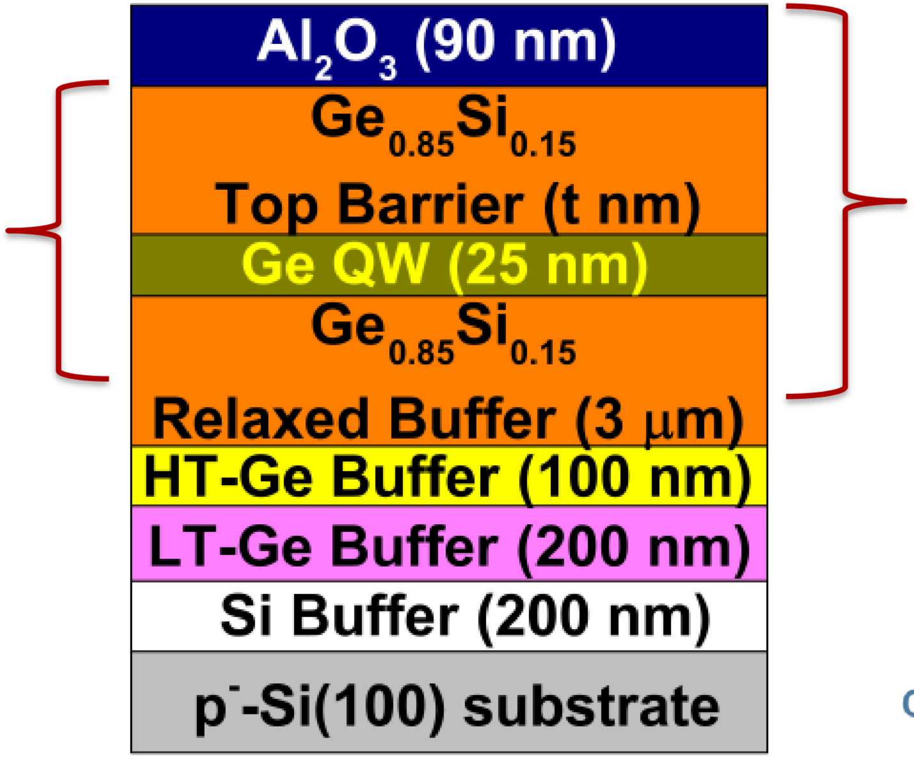


Valance band
2D holes in Ge quantum wells

Properties of Silicon Germanium and SiGe: Carbon. Edited by: Kasper, Erich; Lyutovich, Klara (2000)

Undoped Ge/SiGe heterostructure field-effect transistors




Al_2O_3 (90 nm)

$Ge_{0.85}Si_{0.15}$ Top Barrier (t nm)

Ge QW (25 nm)

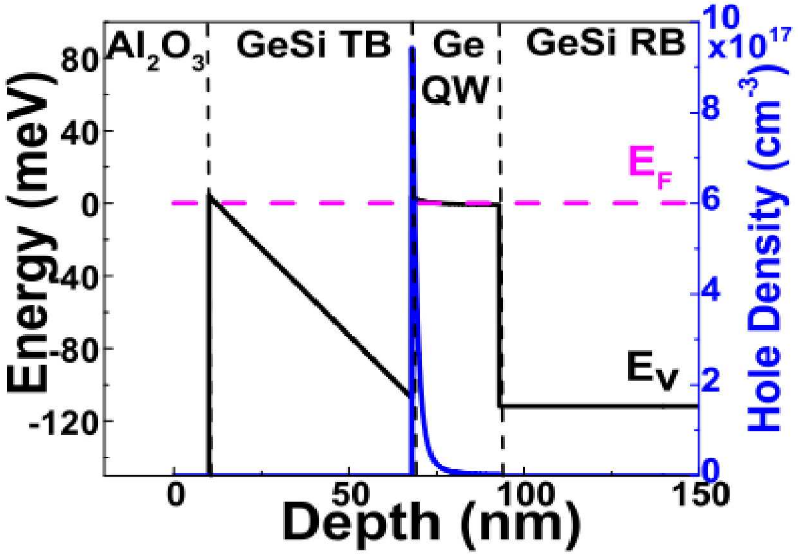
$Ge_{0.85}Si_{0.15}$ Relaxed Buffer (3 μm)

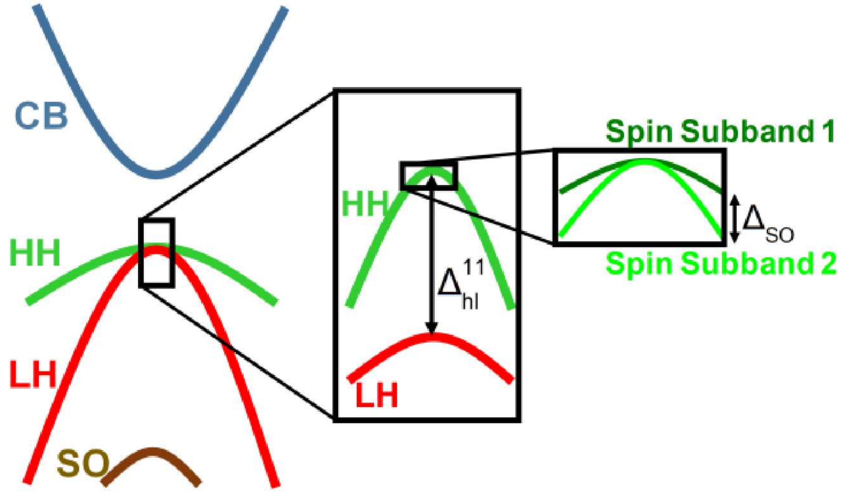
HT-Ge Buffer (100 nm)

LT-Ge Buffer (200 nm)

Si Buffer (200 nm)

p⁻-Si(100) substrate

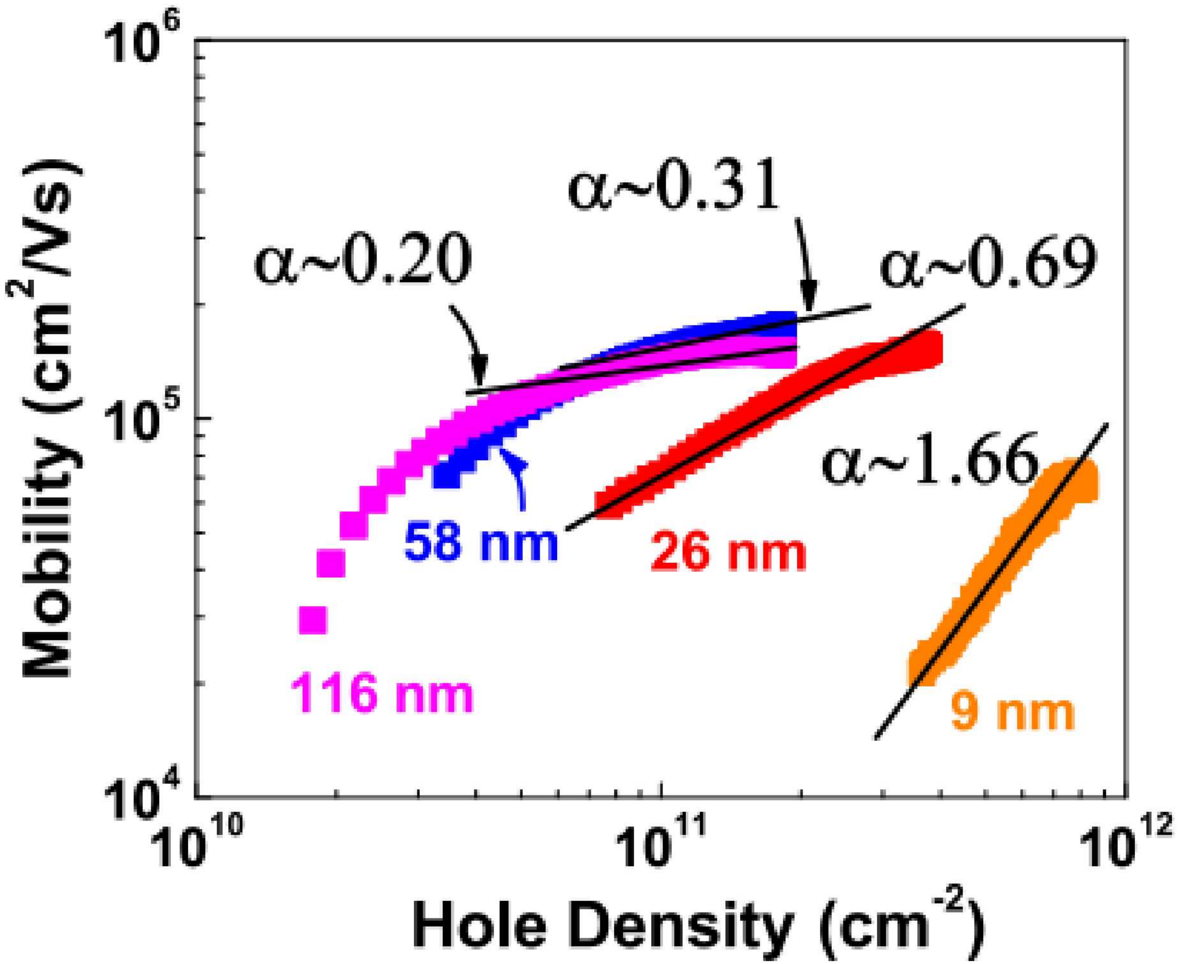




Device operation – mobility

- Mobilty on the order of 2×10^5 cm^2/Vs achievable
- Mobility increases with density
  => screening
- Shallower channels have lower mobilities
  => oxide/GeSi interface is disordered

T = 0.3 K



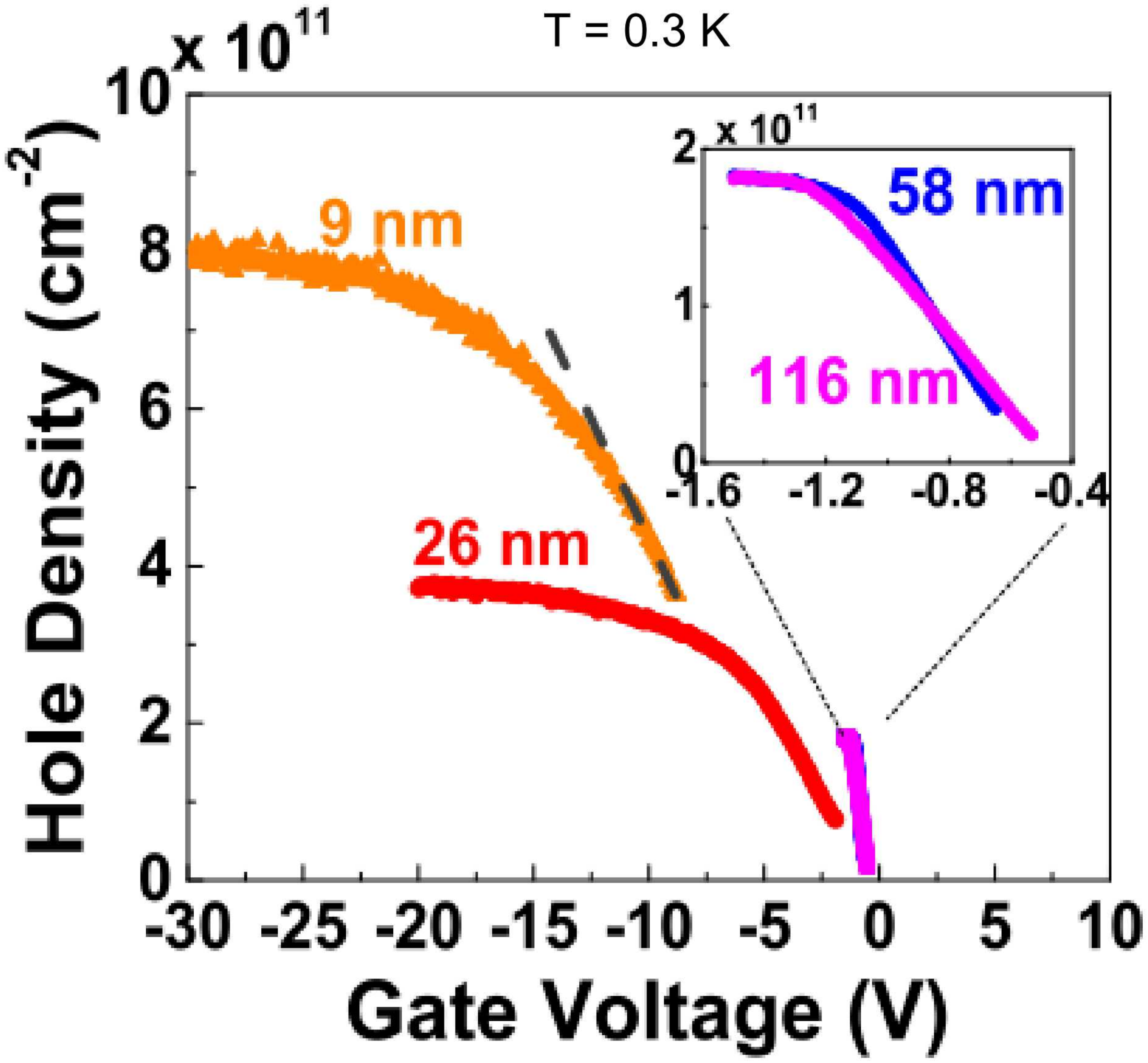
Device operation – 2D hole density

- The 2D hole density saturates.

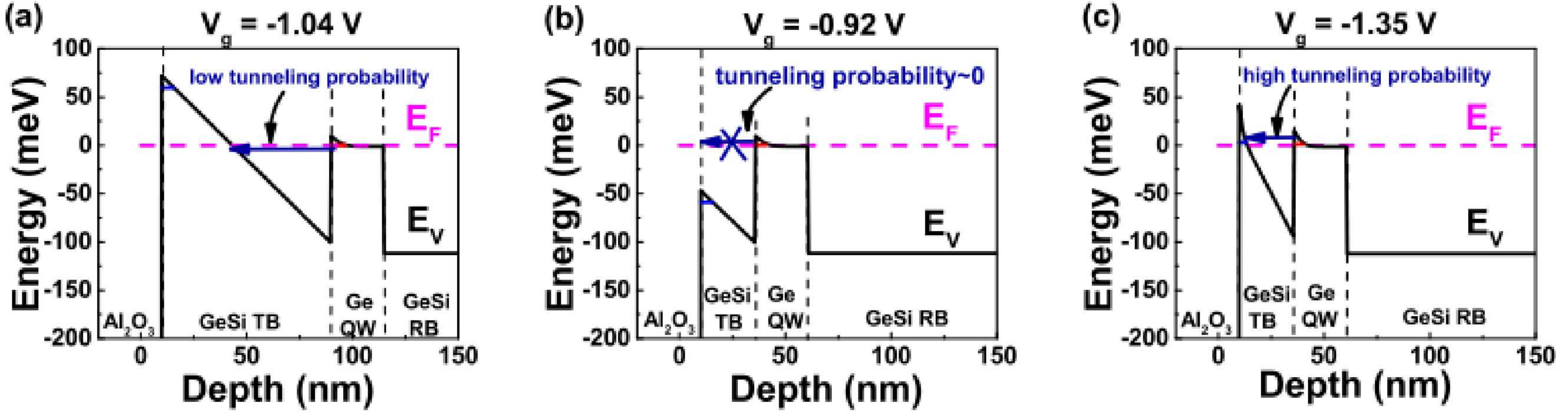
- Shallow channels
  - ➢ High saturation densities, depth dependent.
  - ➢ Small slopes (capacitances)

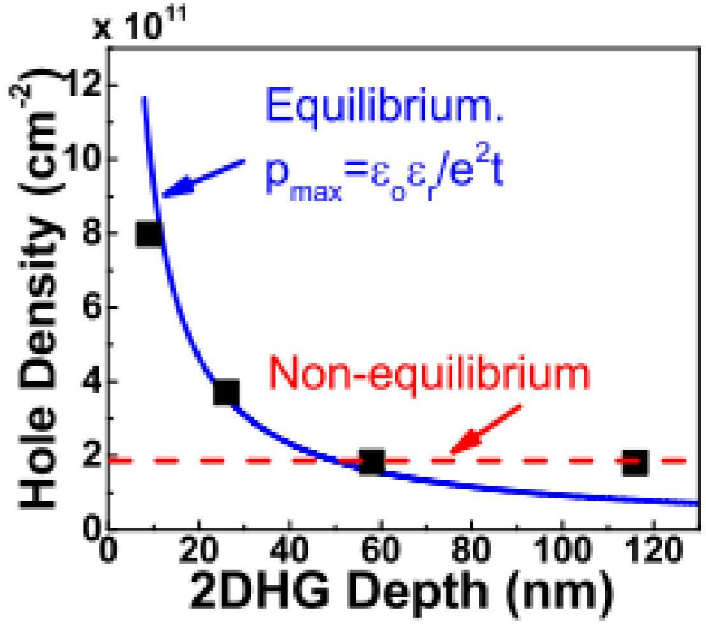
- Deep channels
  - ➢ Low saturation densities, depth independent.
  - ➢ Large slopes (capacitances)

T = 0.3 K



Device operation – 2D hole density





Deep channels

The tunnel rate is limited by triangular barrier (set by Si%) and is depth independent.

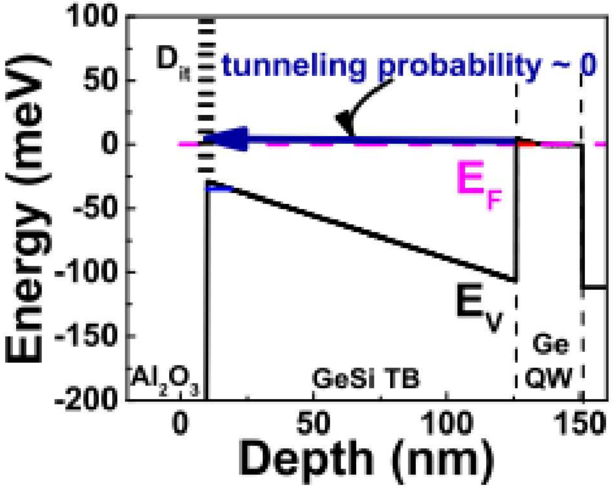
The tunnel rate can be so low that the density only slowly decreases and never reaches equilibrium at low temperatures!

Shallow channels

The tunneling rate is high (compared to experiment time scales).

The density probed by the Hall effect approaches the equilibrium case.

Device operation – 2D hole density

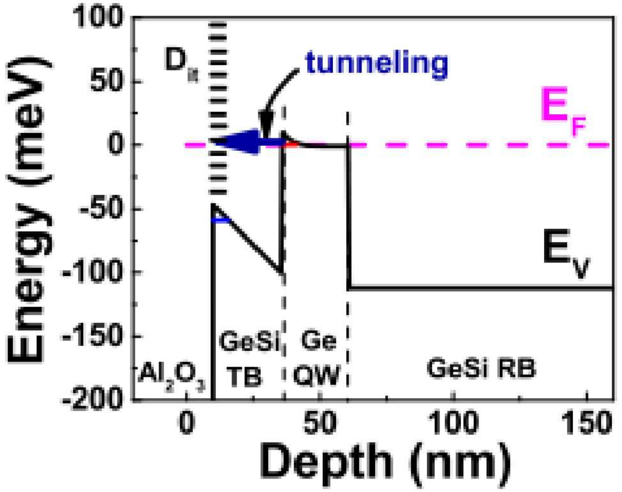


Deep channels

The tunnel rate is low.

The traps at the oxide/GeSi interface do not (need to) get filled.

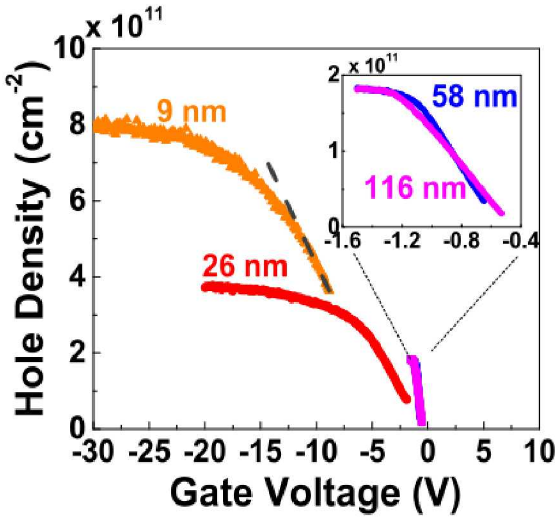
$C_{eff} \sim C_{geometric}$

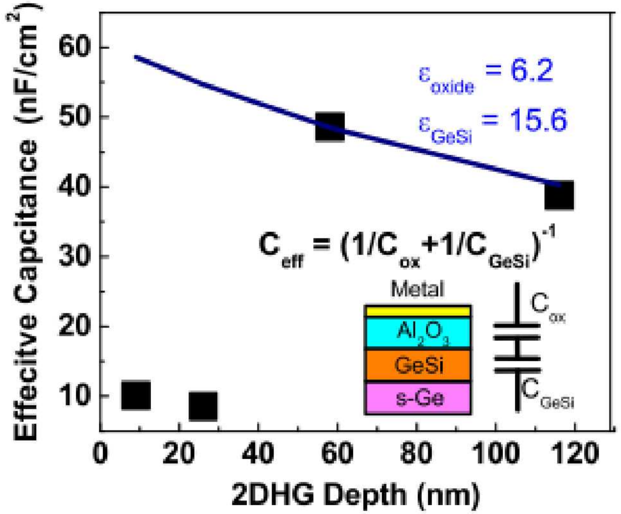


Deep channels

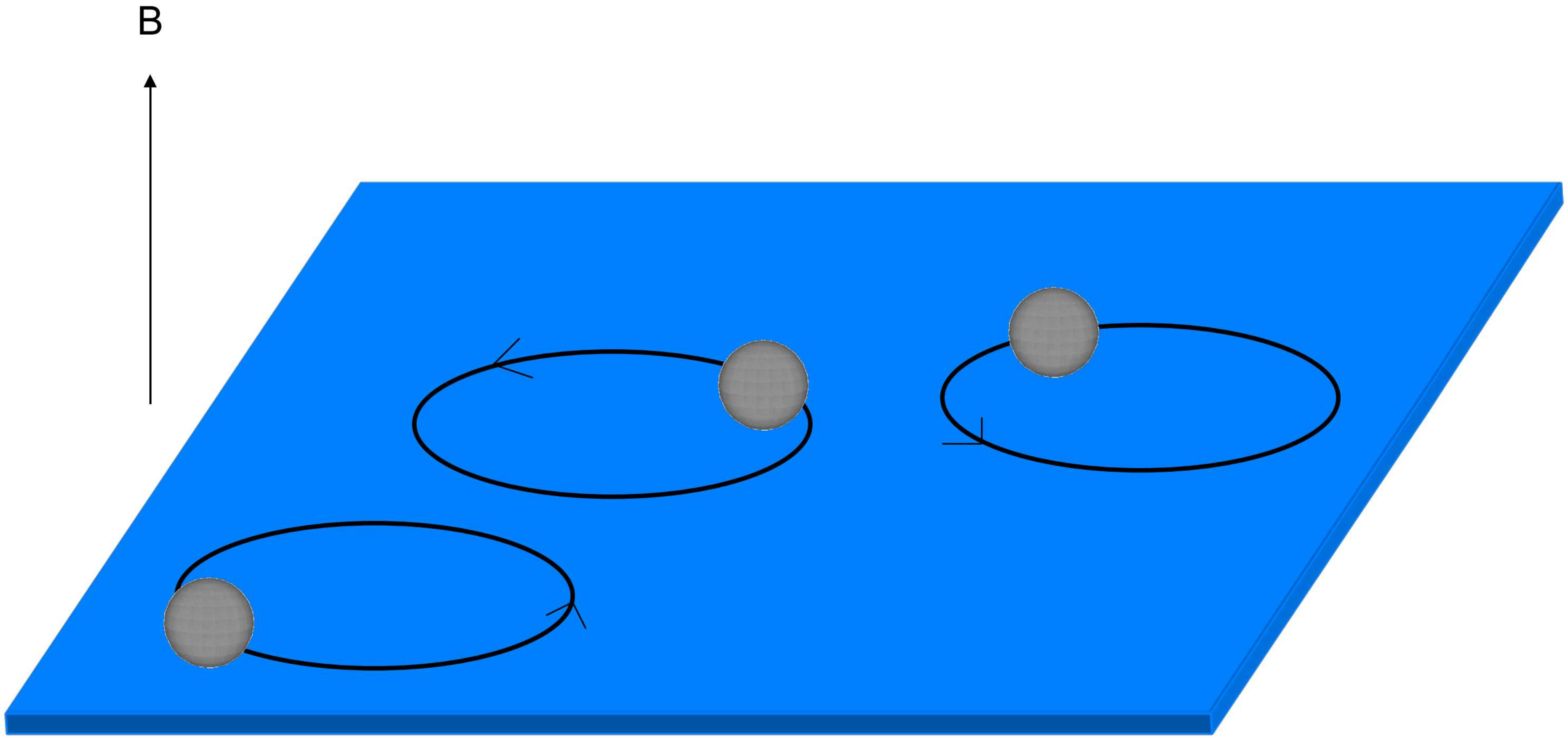
The tunnel rate is high.

The traps at the oxide/GeSi interface need to be filled before the Fermi level can move.





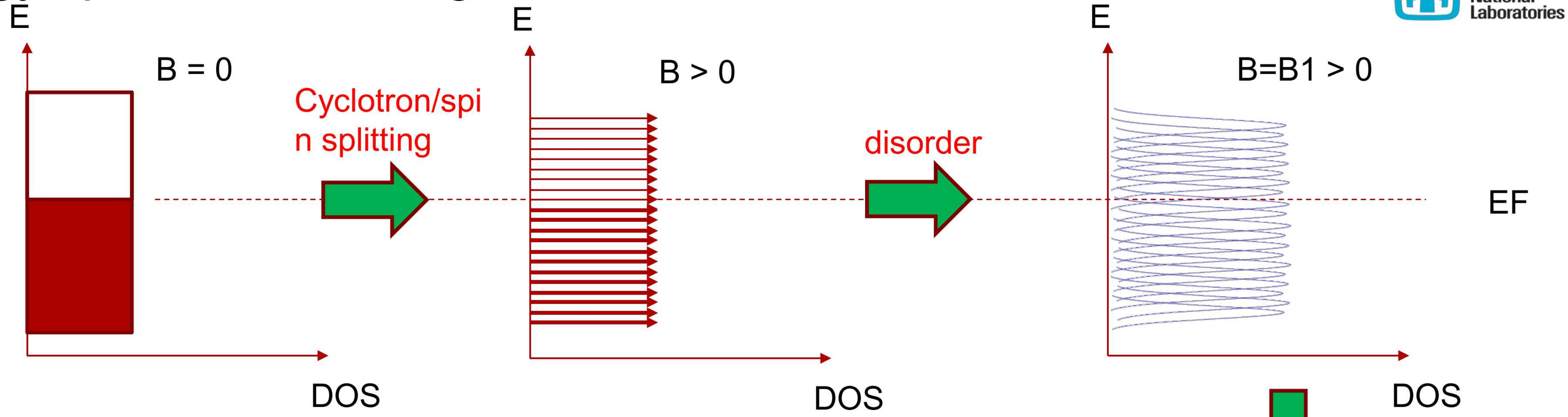
In a perpendicular magnetic field…



Cyclotron motion, $E_c = \hbar e B_{perp}/m^*$

Spin splitting, gap $E_z = g\mu B_{total}$

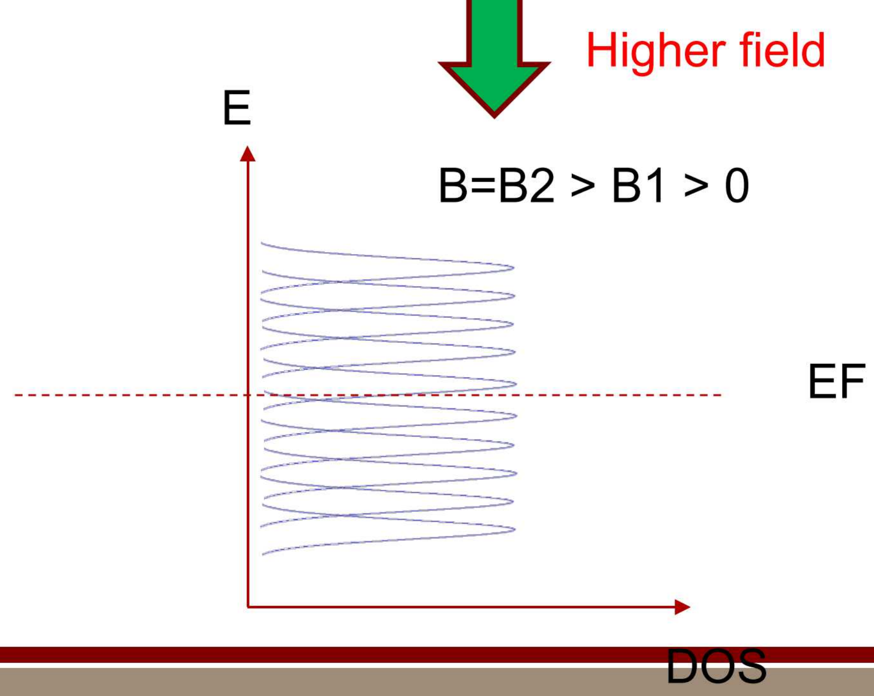
Energy spectrum in a magnetic field



Cyclotron/spin splitting

disorder

Higher field



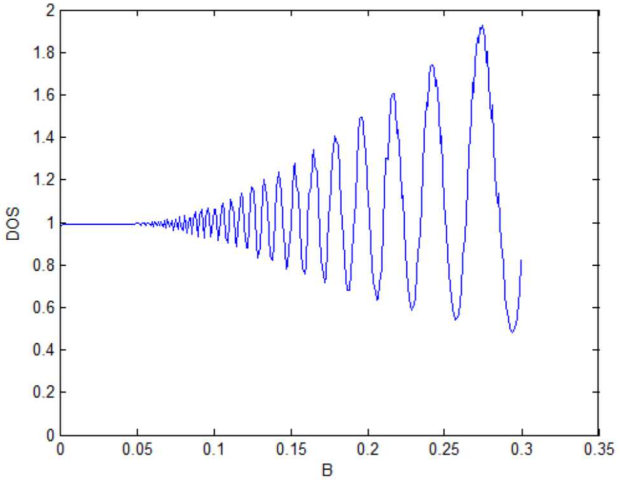
$$\frac{\Delta\rho}{\rho_0} \sim D(X)\,\frac{\Delta DOS}{DOS}$$

$$D(X) = X/\sinh X$$

$$X = 2\pi kT/Gap$$

Temperature dependence
<=> Gap measurement
<=> cyclotron gap or spin gap

DOS at Fermi energy at a fixed density

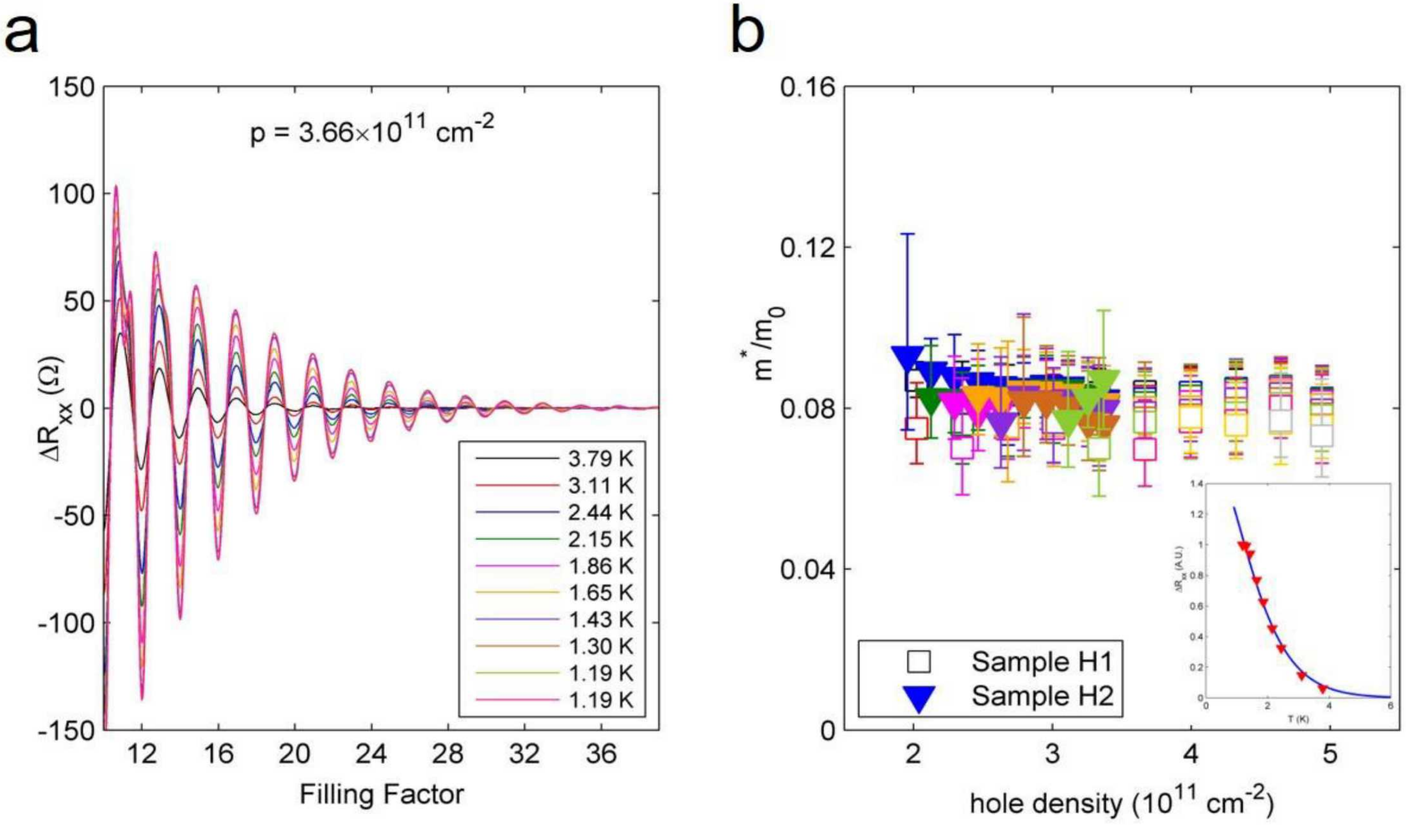


Physical properties – effective mass

- ~ 0.08 m_0.
- ~ density independent.

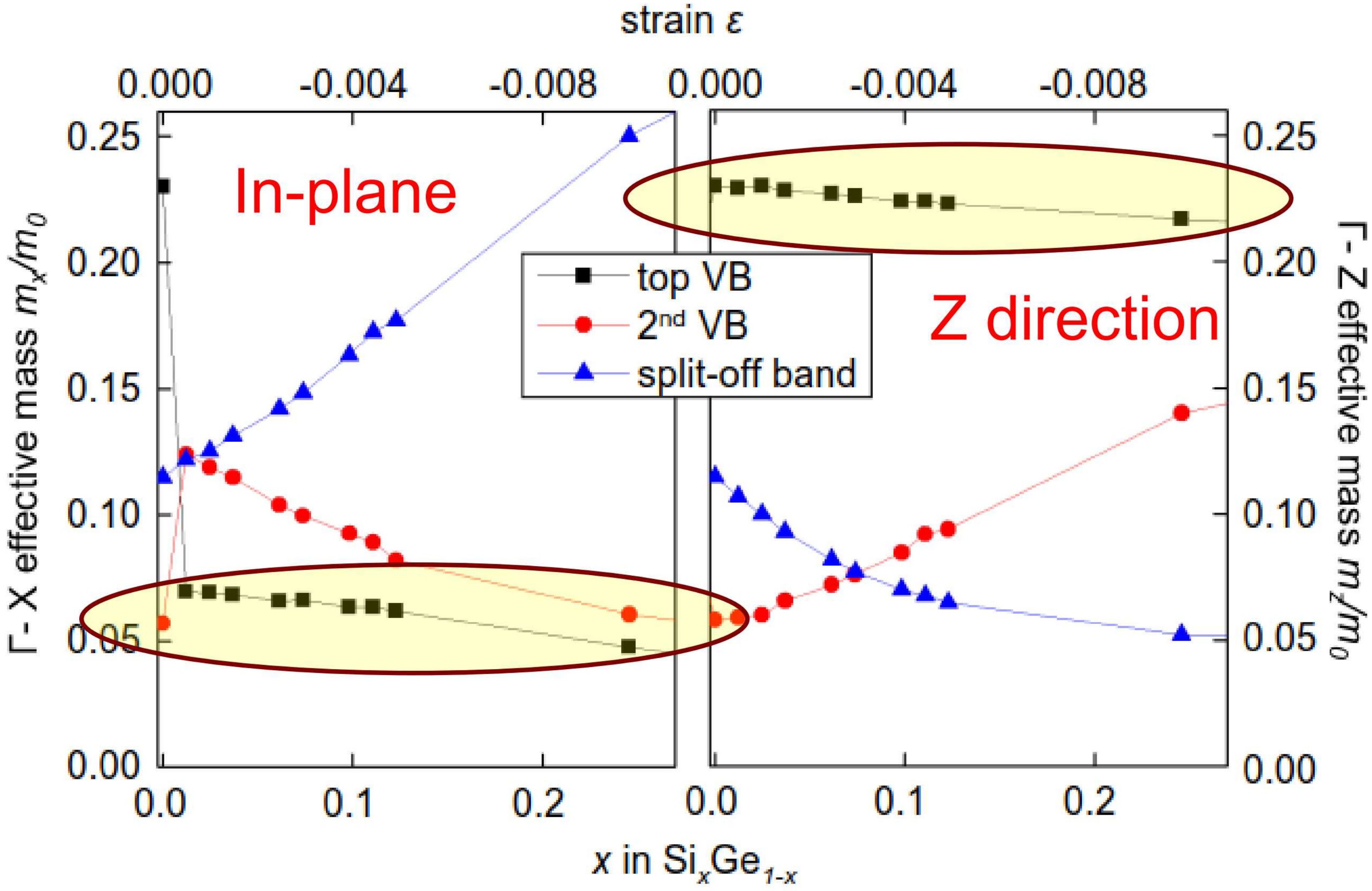
- This mass is small compared to the mass of electrons in Si (0.19), the mass of holes in GaAs (0.2-0.4), and is comparable to the mass of electrons in GaAs (0.07).

- Smaller mass
  => more extended wave functions
  => easier gate controls for nanostructures



Physical properties – effective mass (even filling factors)

Theory



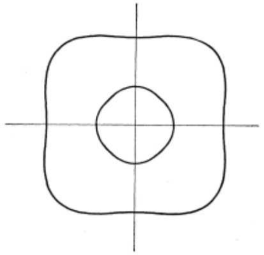


FIG. 8. Figures of constant energy in the (100) plane of k-space for the two fluted energy surfaces which are degenerate at the valence band edge; constants as for germanium.

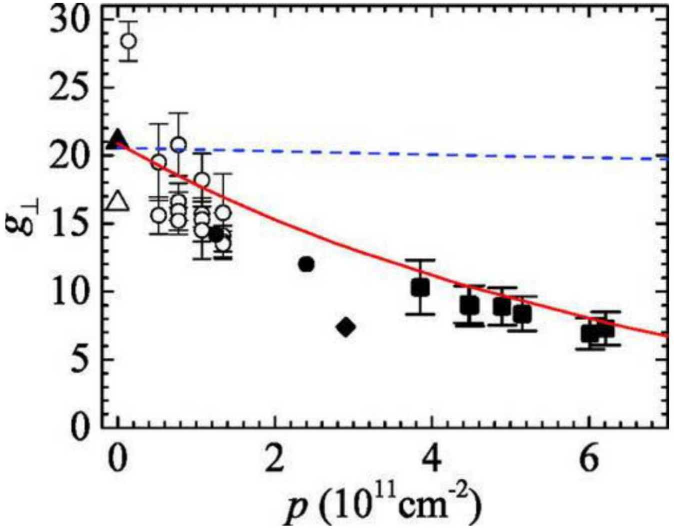
Dresselhaus PR 98, 368

Terrazos arXiv 1803.10320v1

Physical properties – g factor (odd filling factors)

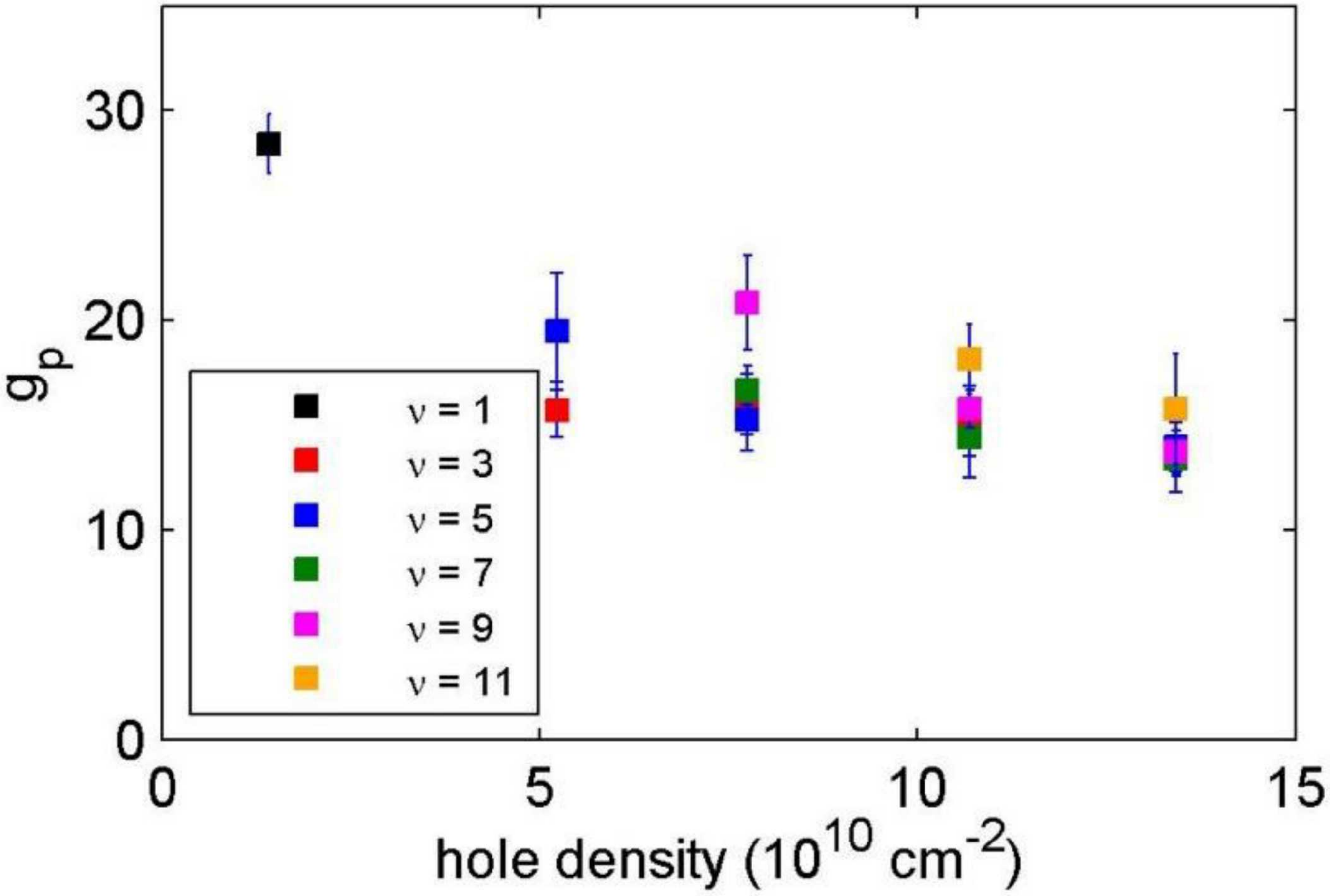
- ~ 10 – 30
- ~ density dependent.

- The g factor is large compared to the g factor of electrons in Si (~2) and the g factor of electrons in GaAs (~0.44).

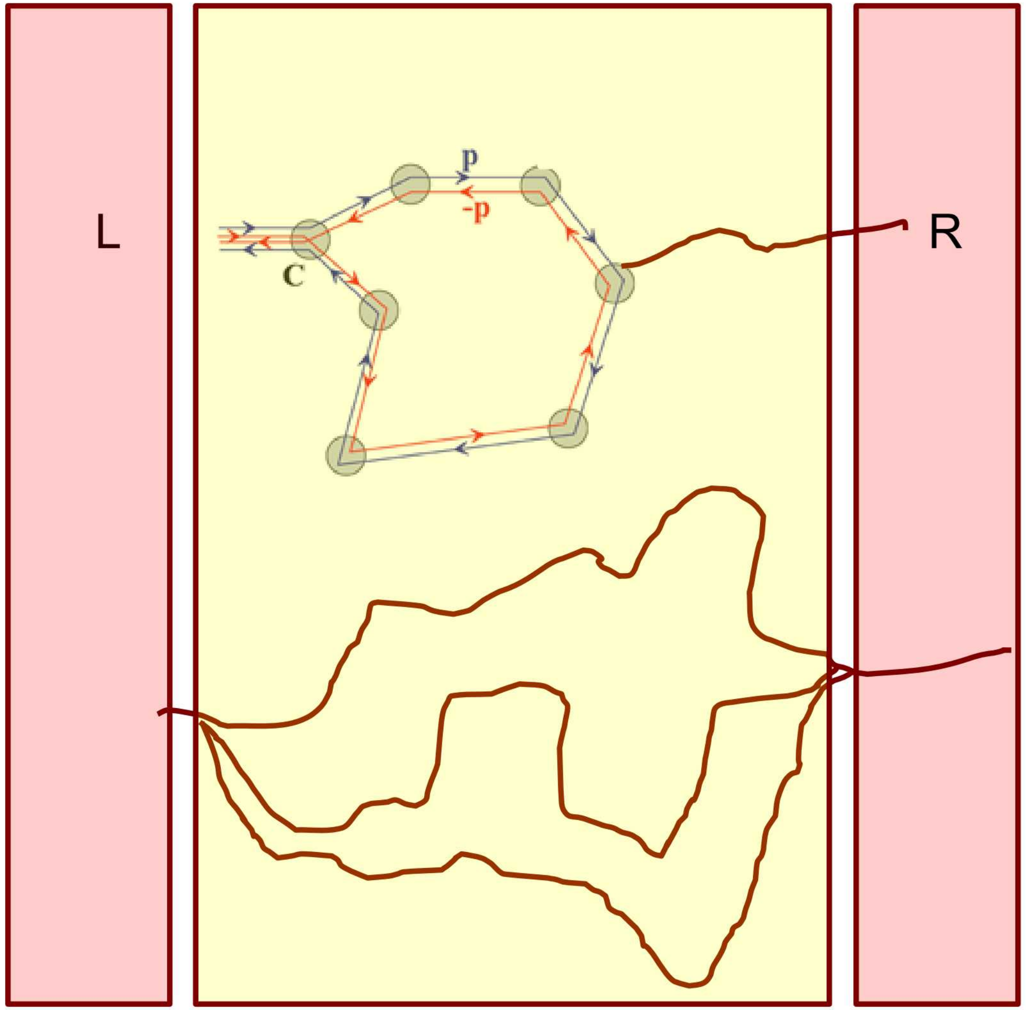


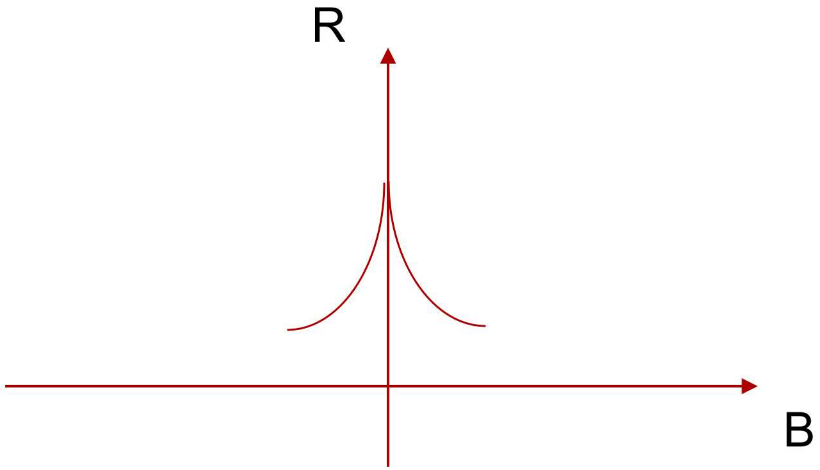
6x6 k.p

Drichko JAP 123, 165703



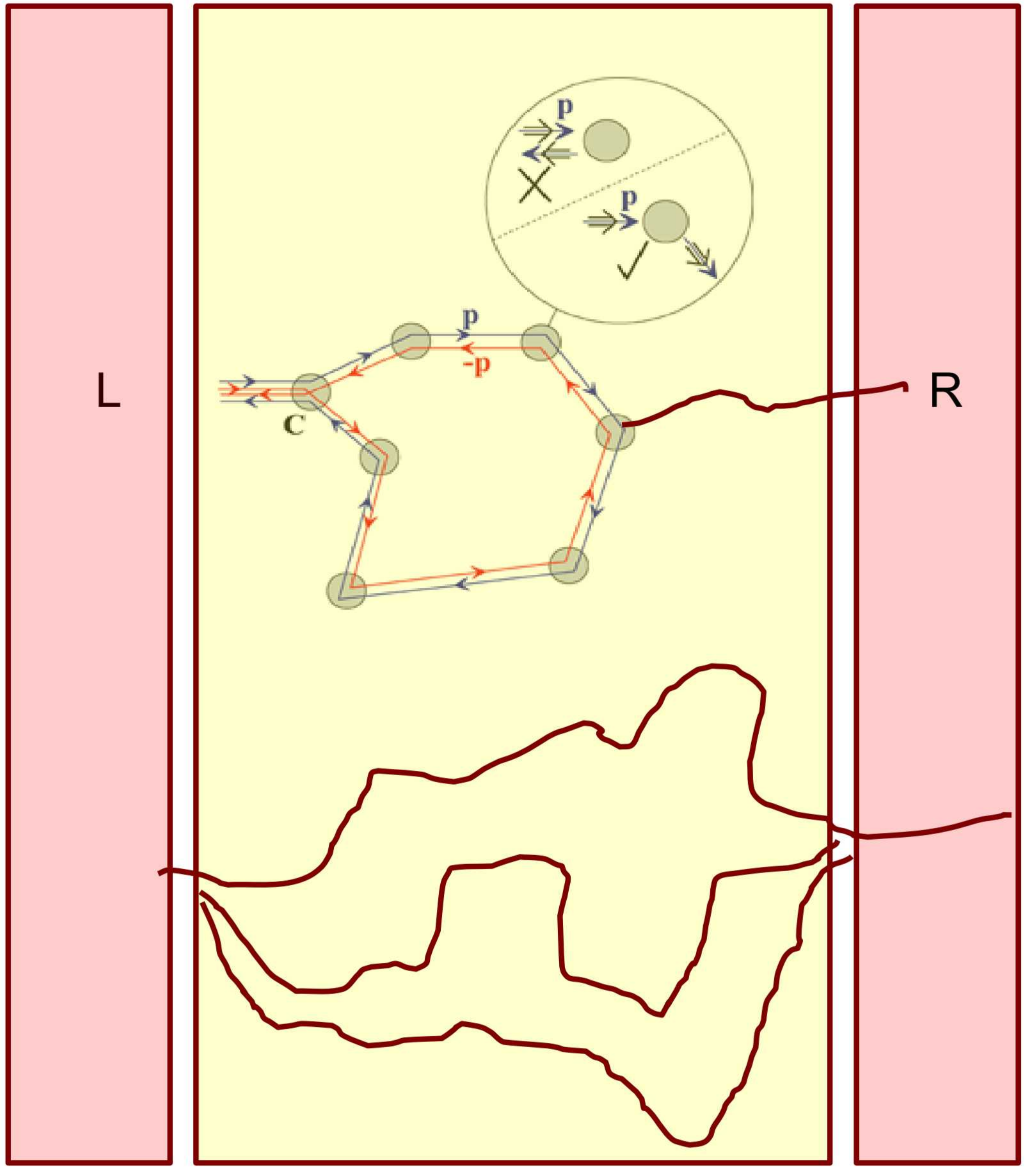
Weak localization (no spin-orbit coupling)



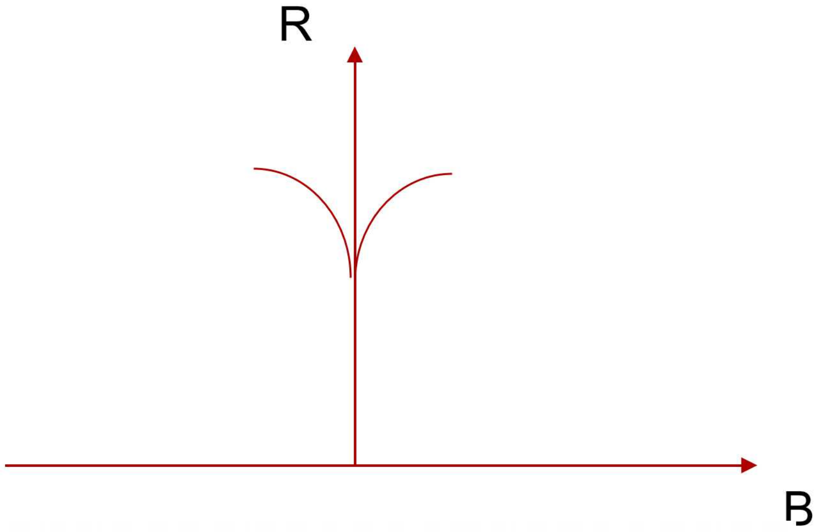


Adapted from McCann Physics 2, 98

Weak anti-localization (spin-orbit coupling)



Spin and momentum are locked together.
Back scattering is suppressed.



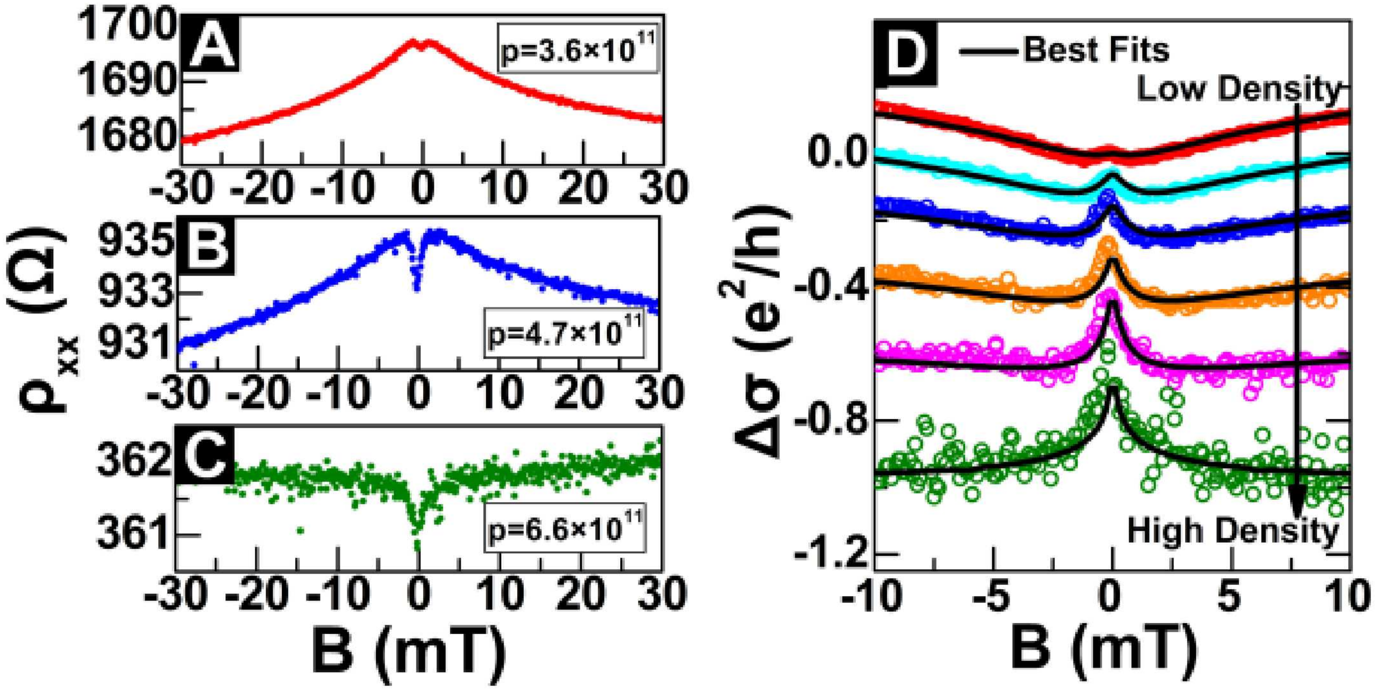
$$\Delta\sigma(B)-\Delta\sigma(0)=\frac{e^2}{2\pi^2\hbar}\left\{\psi\left(\frac{1}{2}+\frac{H_\varphi}{B}+\frac{H_{SO}}{B}\right)+\frac{1}{2}\,\psi\left(\frac{1}{2}+\frac{H_\varphi}{B}+\frac{2H_{SO}}{B}\right)-\frac{1}{2}\,\psi\left(\frac{1}{2}+\frac{H_\varphi}{B}\right)-\ln\frac{H_\varphi+H_{SO}}{B}-\frac{1}{2}\ln\frac{H_\varphi+2H_{SO}}{B}+\frac{1}{2}\ln\frac{H_\varphi}{B}\right\}$$

Hikami Prog. Theor. Phys. 63, 707

Adapted from McCann Physics 2, 98

Physical properties – spin-orbit coupling

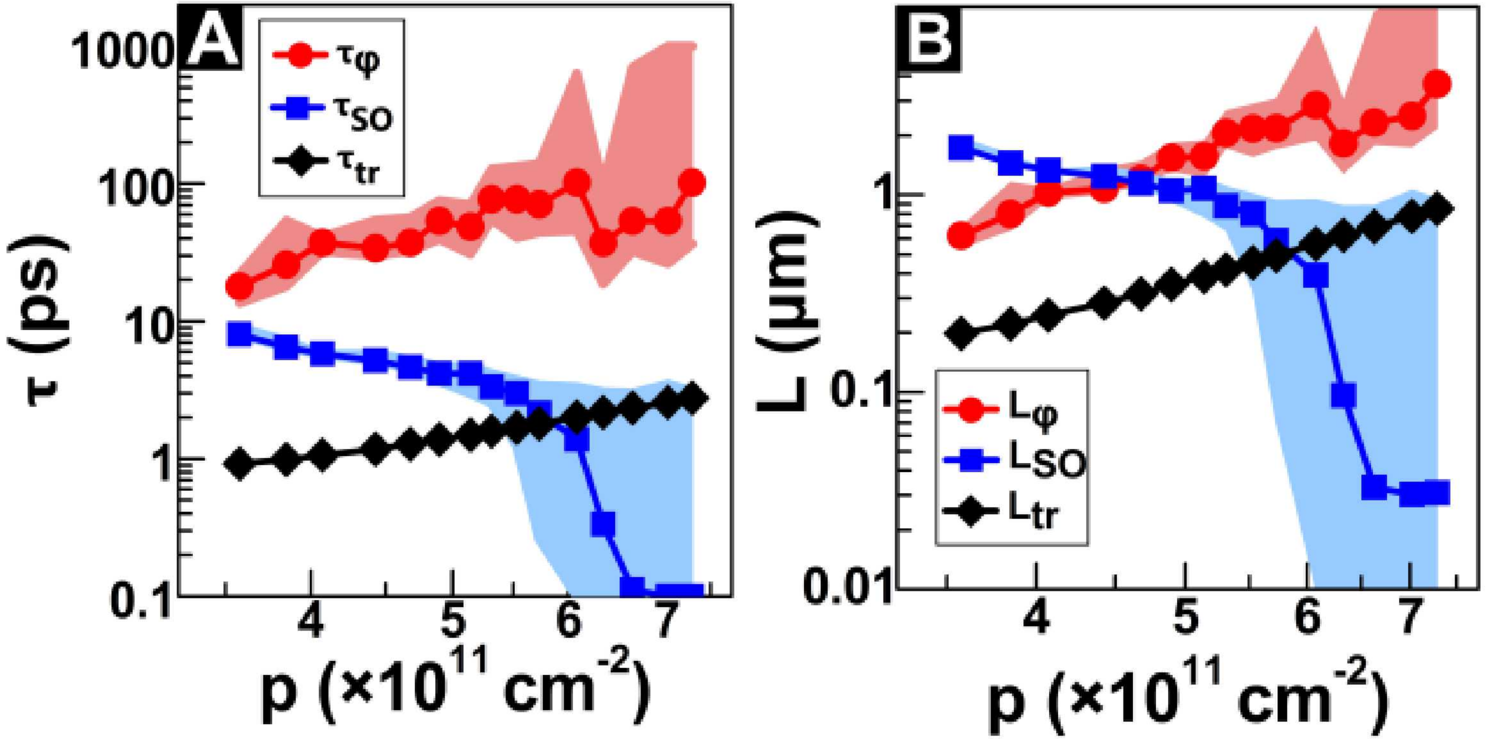
- Low densities
  - Weak localization only
- Intermediate densities
  - Weak anti-localization on top of weak localization only
- High densities
  - Weak anti-localization only



Physical properties – spin-orbit coupling

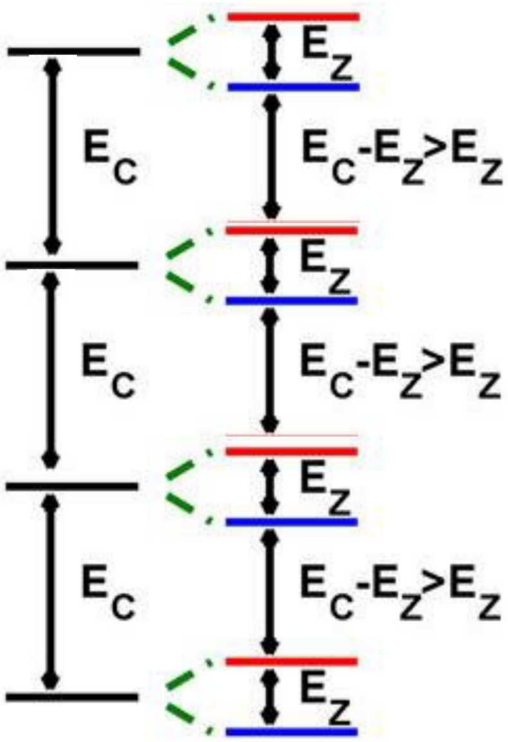
- Spin-orbit length decreases with density and can be as short as 0.1 um (< mean free path), while the phase coherence length can be a few microns long (>mean free path)

- This means the hole spin can rotate at a high yet controlled rate, maintain its phase coherence, and suffer no scattering.



The quantum Hall effect

In a perpendicular magnetic field, the spectrum of a 2D gas is a series of Landau levels:



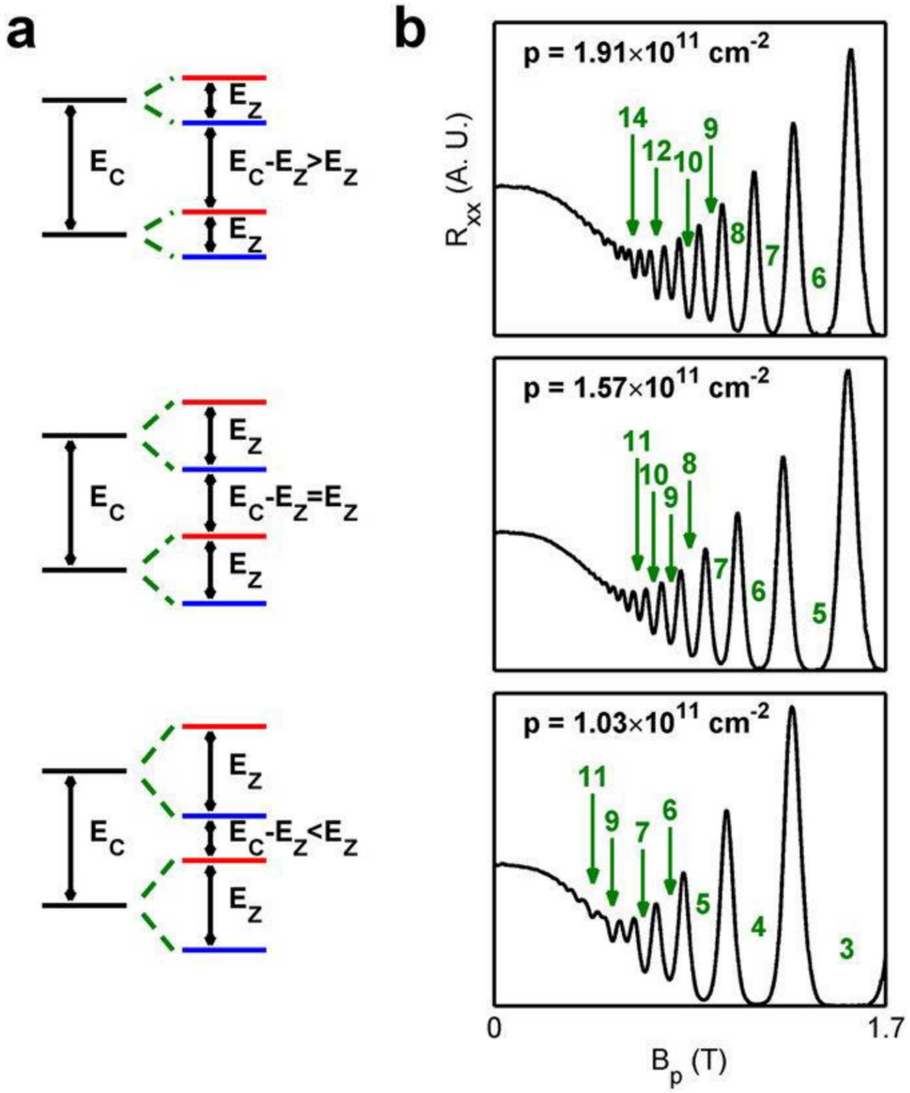
Ec is cyclotron gap: heB/(2πm*)

Ez is Zeeman gap: g*μB

m* and g* are material parameters.

Landau level degeneracy (# electrons / area):
eB/h

Quantum Hall ferromagnetic transition



In most cases, Ec >> Ez

⇒ Strong even states, weak odd states

If Ec ~ 2Ez

⇒ Strength of even states ~ strength of odd states

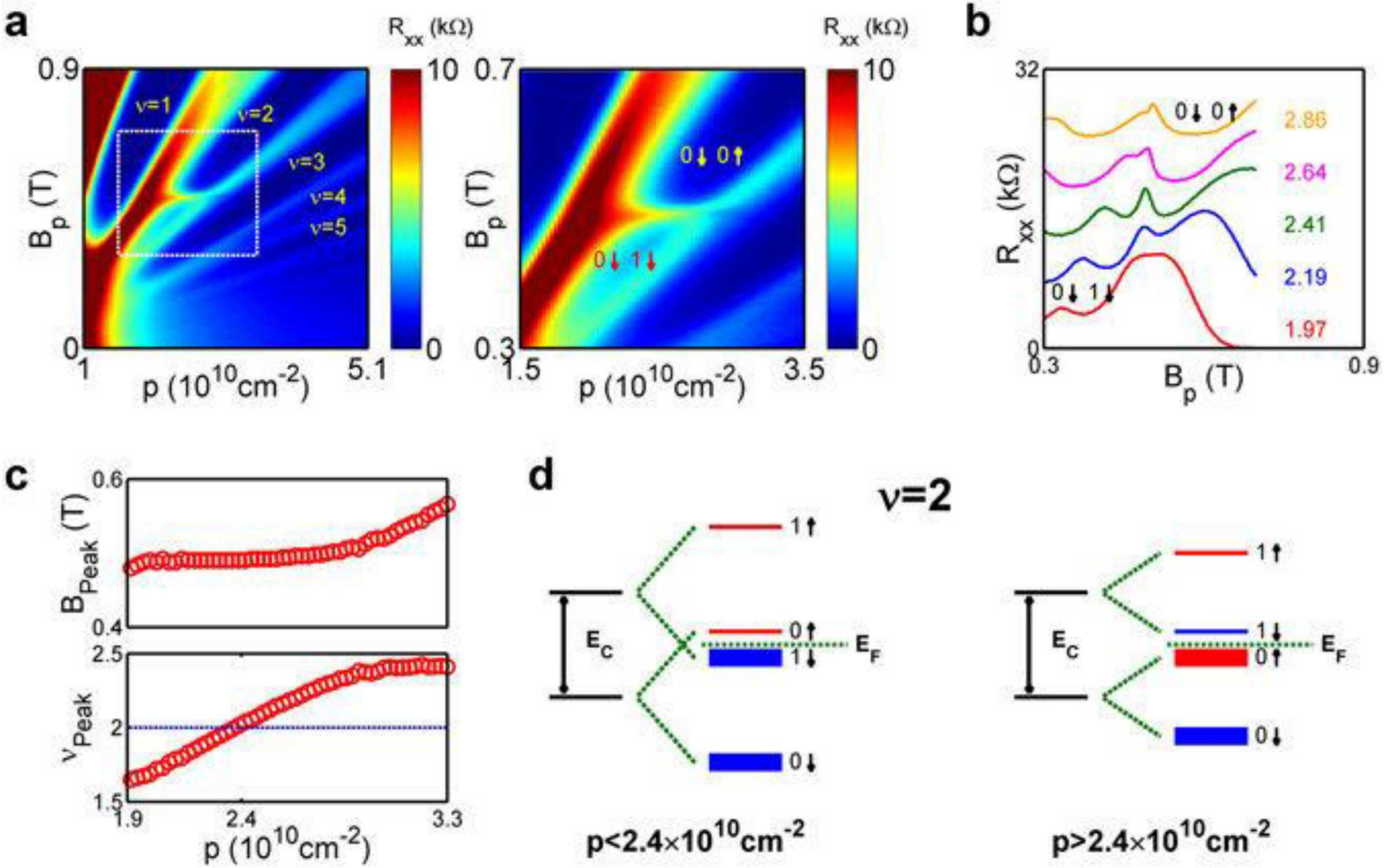
If Ec < 2Ez

⇒ Strong odd states, weak even states

Ez/Ec increases with decreasing density.

Scientific Reports 7, 2468 (2017)

Quantum Hall ferromagnetic transition



A spin transition (unpolarized <-> polarized) at ν=2 occurs at p~2.4x10^{10} cm^{-2}.

This transition marks the point where Ec~Ez

$heB/(2\pi m^*) = g^*\mu B$
$\Rightarrow m^*g^* = 2$

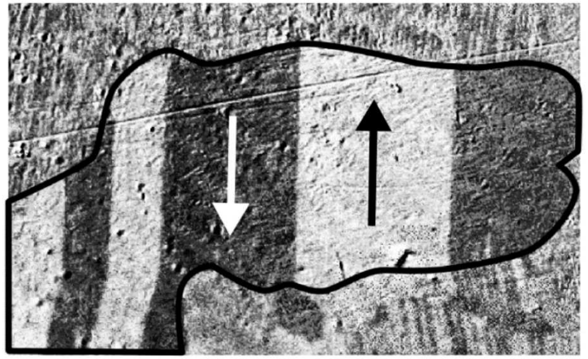
Scientific Reports 7, 2468 (2017)

Quantum Hall ferromagnetic transition

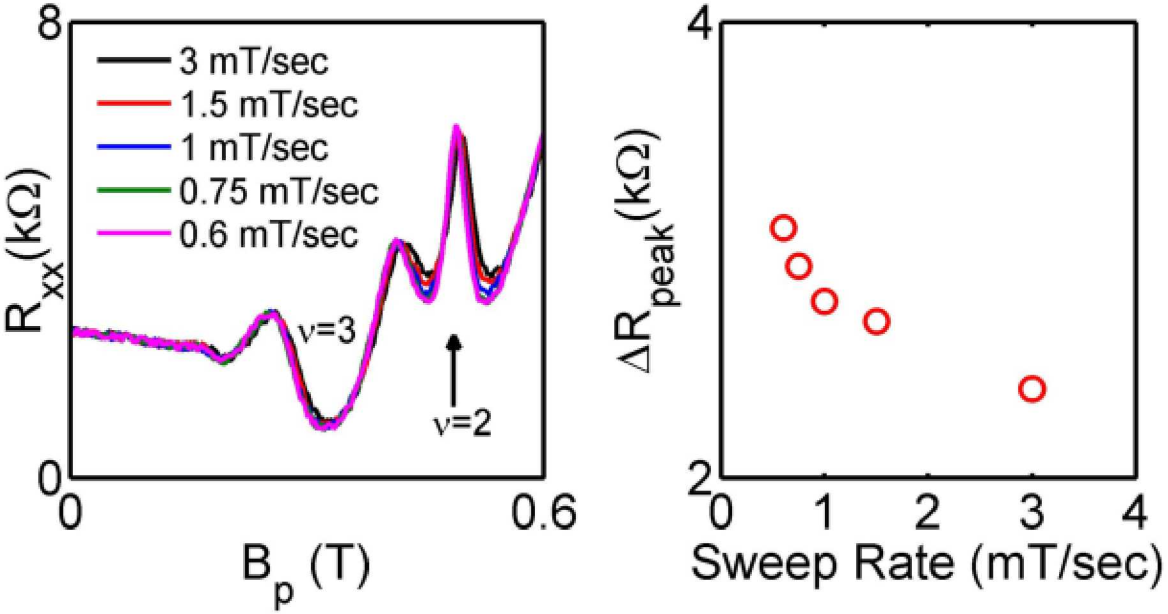
The physical picture of the system at the transition:

micro-domains of different spin configurations. Away from the transition, one spin configuration is preferred. Domains move and merge to minimize surface energy.

Evidence of micro-domains is found in the time dependence.

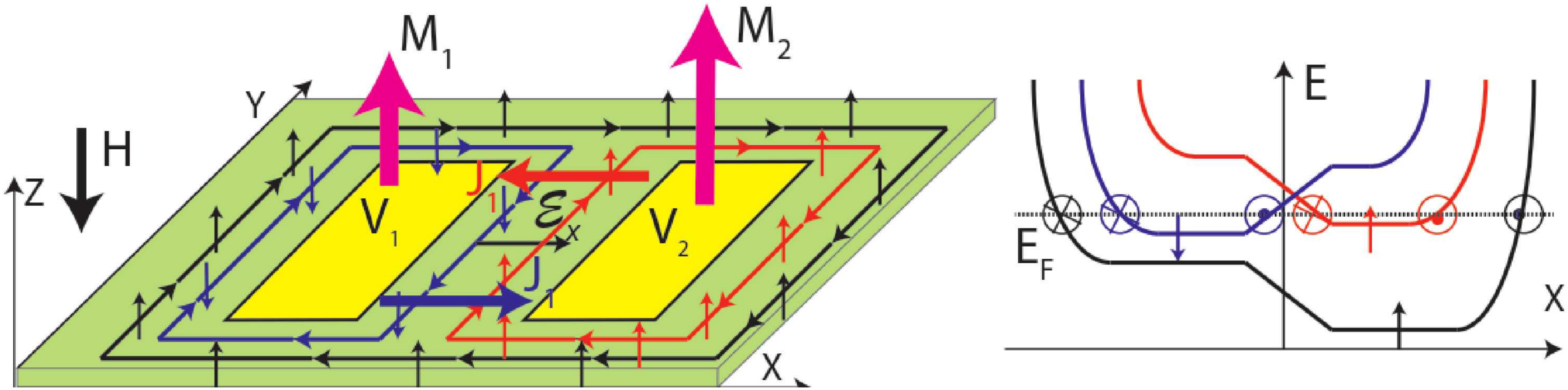


by S. Zurek, E. Magnetica, CC-BY-3.0



Quantum Hall ferromagnetic transition

Local gating to create counter-propagating edge states with opposite spins



Simion arXiv:1707.02929

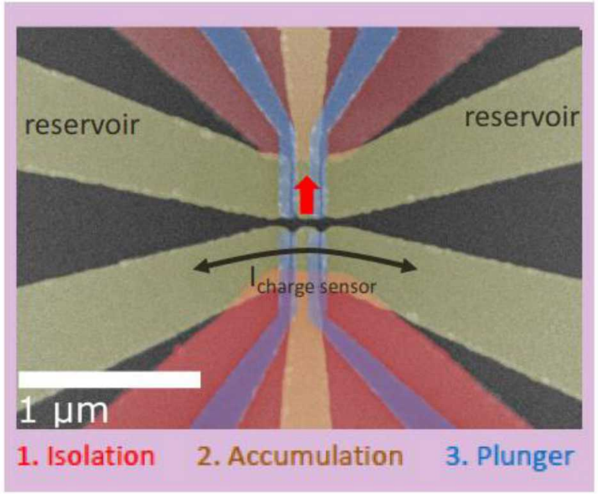
Spin qubits in Ge/SiGe

Implications for Quantum Dots

- Low Disorder
  - Help Dot-Dot Coupling
- Small Effective Mass
  - Help Dot-Dot coupling
  - Easier Lithography
- Anistropic g-factor
  - Large g-factor allows operation at smaller magnetic fields
  - Dot-to-Dot variation is possible
- Strong Spin-Orbit-Coupling
  - Natural mechanism for qubit control
  - Introduces additional noise channel

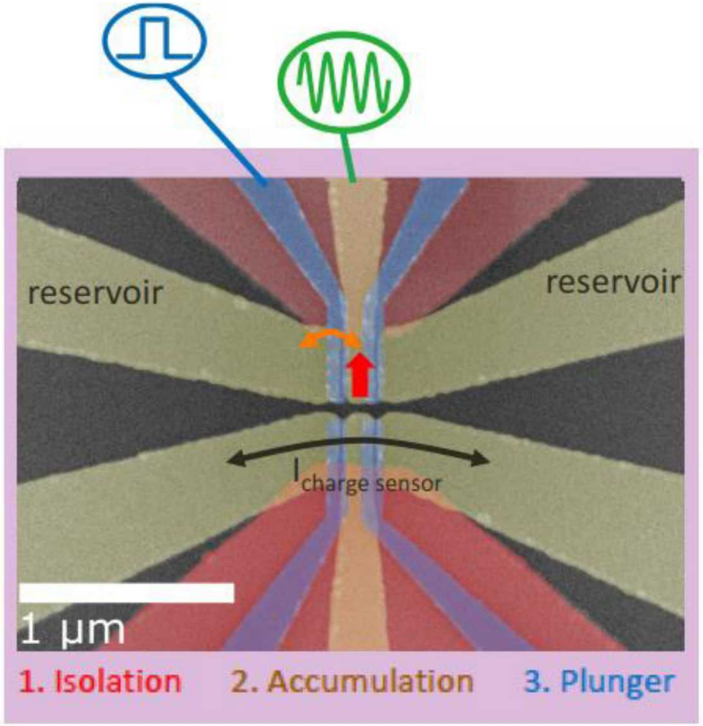
The effect of confinement on these properties remains largely unexplored

Surface electrodes used to laterally confine hole

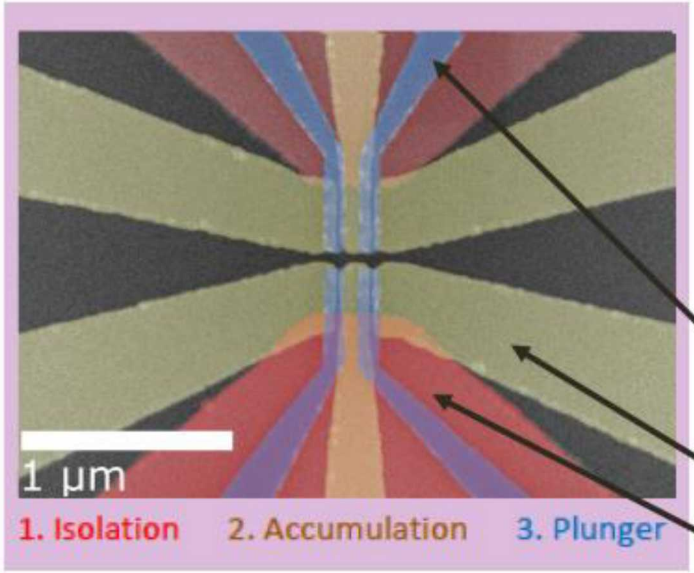


Spin qubits in Ge/SiGe

- Single Hole confined to lateral quantum dot
- Spin Qubit States: $m_j = \pm 3/2$
- Qubit readout and initialization through energy selective tunneling to reservoir
- Qubit Control through microwaves applied to gate
- Occupancy detected through nearby charge sensor

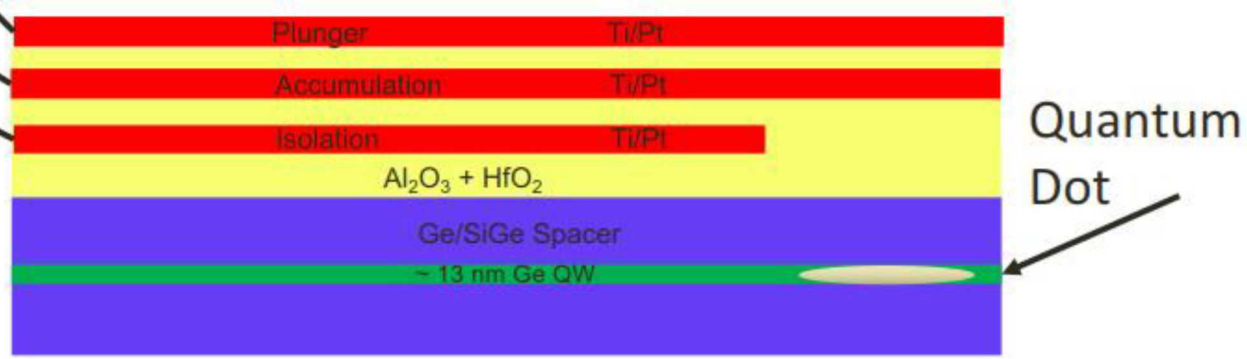


Spin qubits in Ge/SiGe



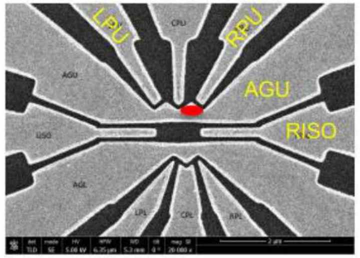
Goals:

- Independent Control of occupation and tunnel barriers
- Tighter Confinement
- Low Capacitance for EDSR

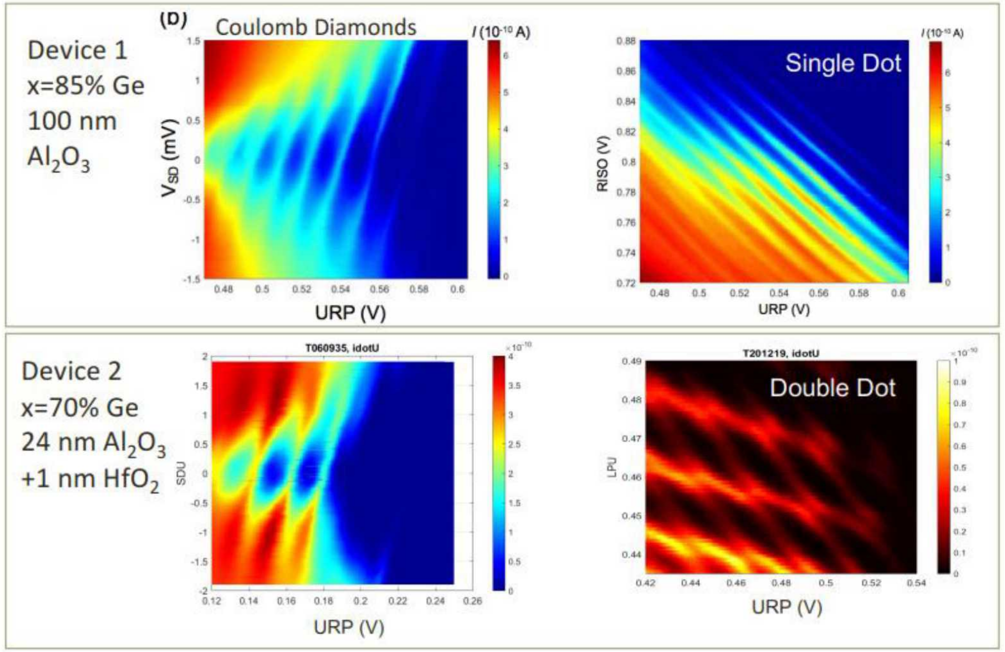


Ga implanted Ohmic contacts

Spin qubits in Ge/SiGe

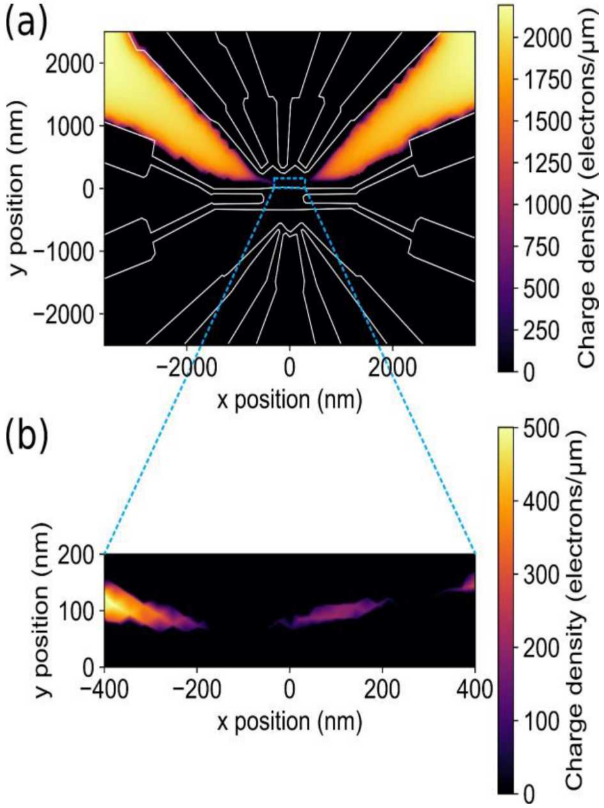


Single Layer Devices can be tuned to low-hole regime in transport



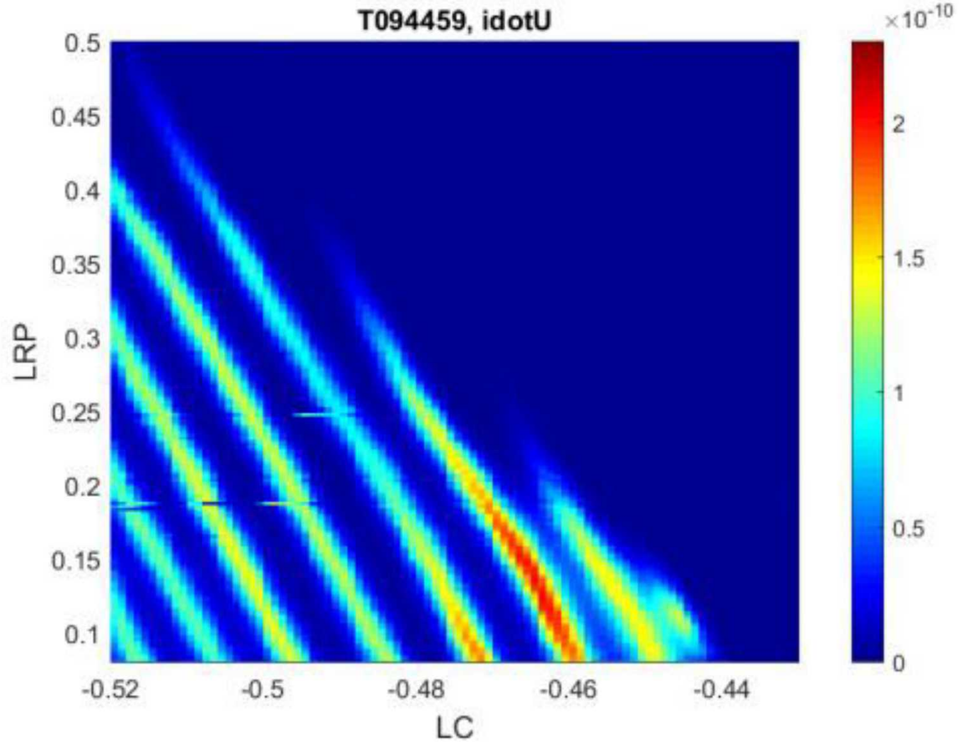
Device 1
x=85% Ge
100 nm
Al_2O_3

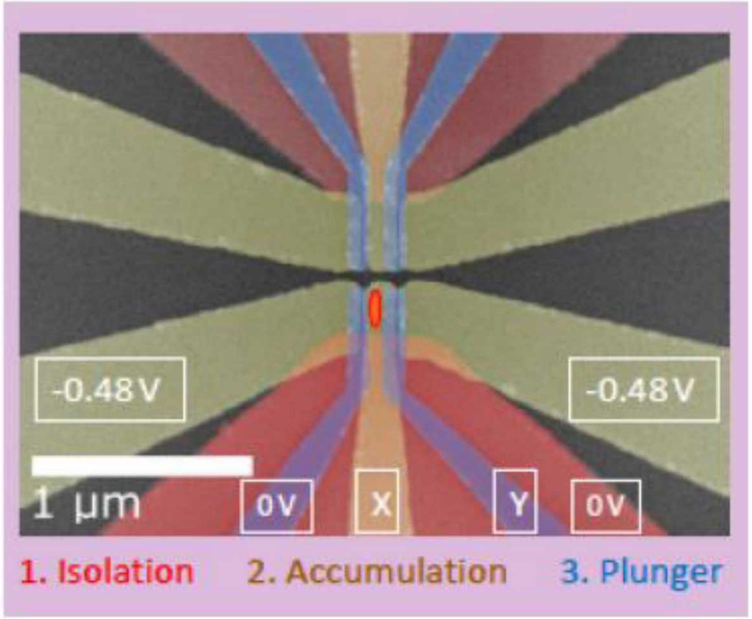
Device 2
x=70% Ge
24 nm Al_2O_3
+1 nm HfO_2



Spin qubits in Ge/SiGe

Three Metal Layer Device





Coulomb Blockade observed in the three-metal-layer devices

Summary

- Induced 2D holes in Ge/SiGe heterostructure field effect transistors demonstrated.
- Device behavior can deviate from thermal equilibrium.
- Physical properties (mass, g factor, spin-orbit coupling strength) characterized.
- Gate controlled quantum Hall ferromagnetic transition observed at low densities.
- Development of spin qubits in Ge/SiGe

Acknowledgements

- Sandia National Laboratories: M. P. Lilly, D. Laroche, L. A. Tracy, C. T. Harris, N. T. Jacobson, J. Moussa, A. D. Baczewski, D. R. Luhman, W. Hardy, and L. N. Maurer.
- National Taiwan University: C. W. Liu, J.-Y. Li, C.-H. Lee, S.-H. Huang, Y. Chuang, Y.-H. Su, C.-T. Chou
- NHMFL

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